of <u>3</u> FORM PTO 1449 (modified) ATTY DOCKET NO. 017835/0342 522 Rec'd PCT/PTO 2 2 JAN 1999 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE APPLICANT Bruno FRANCOEUR et el. LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary) FILING DATE GROUP January 22, 1999 Unknown Date Submitted to PTO: April 22, 1999 U.S. PATENT DOCUMENTS CLASS SUBCLASS FILING DATE IF **EXAMINER** DOCUMENT DATE NAME INITIAL NUMBER APPROPRIATE 06/02/87 363 132 4,670,833 Sachs A1 4,755,910 07/05/88 Val 361 401 АЗ 4,907,068 03/06/90 Amann et al. 357 74 08/27/91 363 147 A4 5,043,859 Korman et al. 07/21/92 363 5,132,896 Nishizawa et al. 144 **A5** 5,142,439 08/25/92 Huggett et al. 361 321 A6 5,170,337 12/08/92 Borowiec et al. 363 147 04/13/93 Hideshima 257 685 **A8** 5,202,578 05/17/94 361 710 5.313.363 Arbanas 49 5,347,158 09/13/94 Matsuda et al. 257 691 A10 132 5,414,616 05/09/95 Hatozaki 363 . 257 690 06/13/95 Arai et al. A12 5.424.579 07/04/95 257 690 A13 5,430,326 Miyashita FOREIGN PATENT DOCUMENTS TRANSLATION DOCUMENT DATE COUNTRY CLASS **SUBCLASS** NUMBER YES NO OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.) 10-26-04 DATE CONSIDERED EXAMINER Oary

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<sup>\*</sup>EXAMINER: Initial if reference donsidered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered.

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